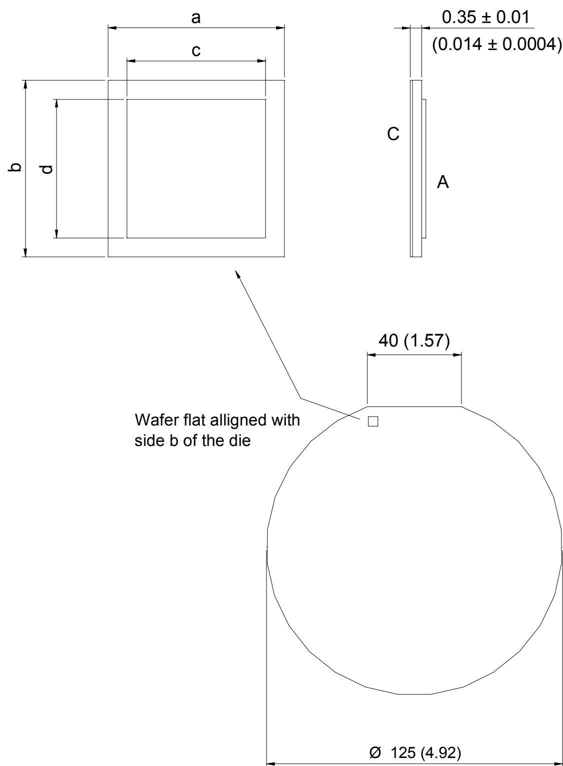
International
IOR Rectifier

FD160H06A5B

Fred Die in Wafer Form



NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

2. CONTROLLING DIMENSION (INCH):

3. DIMENSIONS AND TOLERANCES:
a = 4.064 ± 0.05
(0.160 ± 0.002)
b = 4.064 ± 0.05
(0.160 ± 0.002)
c = 3.404 ± 0.003
(0.134 ± 0.0001)
d = 3.404 ± 0.003
(0.134 ± 0.0001)

4. LETTER DESIGNATION:
A = Anode (Top Metal)
C = Cathode (Back Metal)

5. SAWING:
Recommended Blade
SEMITEC S1025 QS00 Blade

6. MINIMUM ORDER QUANTITY:
500 die

NOT TO SCALE

Reference IR Packaged Part: 30ETH06/ 30EPH06 Series

Electrical Characteristics (Wafer Form)

	Parameters	Units	Test Conditions
V_{FM}	Maximum Forward Voltage	2.3 V	T_J = 25°C, I_F = 30 A
V_{RRM}	Mimunum Reverse Breakdown Voltage	600 V	T_J = 25°C, I_{RRM} = 200 µA
I_{RM}	Max. Reverse Leakage Current	100µA	T_J = 25°C, V_{RRM} = 600 V
t_{rr}	Typ. Reverse Recovery Time	20 ns	I_F = 1A, di/ dt = 100A/µs, V_R = 30 V

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 2 KA - 3 KA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.160" x 0.160" (see drawing)
Reject Ink Dot Size	0.25 mm diameter minimum
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code

FD	160	H	06	A	5	B
1	2	3	4	5	6	7

1	- Fred Die			
2	- Chip Dimension in Mils:	160	=	160x160 square
3	- Process:	H	=	HyperFast
4	- Voltage code Vrrm (*100) eg:	06	=	600V
5	- Chip surface metallization:	A	=	Aluminium (anode), Silver (cathode)
6	- Wafer diameter in inches			
7	- Packaging:	B	=	Inked Probed Unsawn Wafer (Wafer in box)